



70V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)}	I _D T _A = +25°C	
-70V	160m Ω @ V _{GS} = -10V	-2.6A	
-700	250m Ω @ V _{GS} = -4.5V	-1.6A	

Description

This MOSFET has been designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- · Transformer Driving Switch
- DC-DC Converters
- Power Management Functions
- Uninterrupted Power Supply

Features and Benefits

- 100% Unclamped Inductive Switch (UIS) test in production
- Low On-Resistance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 5)

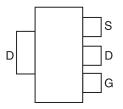
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See diagram below
- Terminals: Finish Matte Tin annealed over Copper lead frame.
 Solderable per MIL-STD-202, Method 208 3
- Weight: 0.112 grams (approximate)

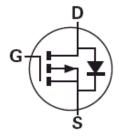
SOT223







Pin Out - Top View



Equivalent Circuit

Ordering Information (Note 4)

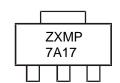
Part Number	Qualification	Case	Packaging
ZXMP7A17GTA	Commercial	SOT223	1,000/Tape & Reel
ZXMP7A17GQTA	Automotive	SOT223	1,000/Tape & Reel

Notes:

Downloaded from **Arrow.com**.

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http"//www.diodes.com/products/packages.html
- 5. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_grade_definitions/.

Marking Information



ZXMP7A17 = Product Type Marking Code



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-70	V
Gate-Source Voltage			V _{GS}	±20	V
		(Note 7)		-3.7	
Continuous Drain Current	$V_{GS} = 10V$	$T_A = +70^{\circ}C \text{ (Note 7)}$	I_{D}	-2.9	Α
		(Note 6)		-2.6	
Pulsed Drain Current	V _{GS} = 10V	(Note 8)	I _{DM}	-9.6	А
Continuous Source Current ((Body diode)	(Note 7)	Is	-4.8	А
Pulsed Source Current (Body diode) (Note 8)		I _{SM}	-9.6	Α	

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 6)	D.	2.0 16.0	W	
Linear Derating Factor	(Note 7)	P _D	3.9 31	mW/°C	
Thermal Resistance, Junction to Ambient	(Note 6) (Note 7)	R ₀ JA	62.5 34	°C/W	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

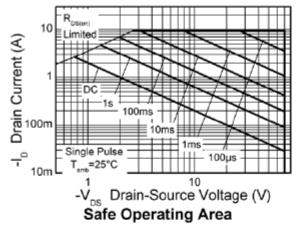
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

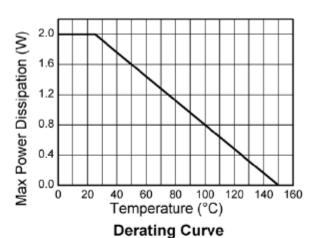
Characteristic	Symbol	Min	Тур	Max	Unit	Test C	ondition	
OFF CHARACTERISTICS								
Drain-Source Breakdown Voltage	BV _{DSS}	70	_	_	V	I _D = -250μA, V _{GS} = 0V		
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μΑ	V _{DS} = -70V, V _{GS} =	= 0V	
Gate-Source Leakage	Igss	_	_	100	nA	V _{GS} = ±20V, V _{DS}	= 0V	
ON CHARACTERISTICS	_							
Gate Threshold Voltage	V _{GS(th)}	-1.0	_	_	V	I_{D} = -250 μ A, V_{DS}	= V _{GS}	
Static Drain-Source On-Resistance (Note 9)	D			0.16	Ω	V_{GS} = -10V, I_{D} = -	·2.1A	
Static Dialif-Source Off-Resistance (Note 9)	R _{DS(ON)}	_	_	0.25	12	V_{GS} = -4.5V, I_{D} =	-1.7A	
Forward Transconductance (Notes 9 & 10)	g fs	_	4.4	_	S	V _{DS} = -15V, I _D = -	·2.1A	
Diode Forward Voltage (Note 9)	V _{SD}	_	-0.85	-0.95	V	I _S = -2.0A, V _{GS} =	I _S = -2.0A, V _{GS} = 0V	
Reverse recovery time (Note 10)	t _{rr}		29.8	_	ns	I _S = -2.1A, di/dt= 100A/µs		
Reverse recovery charge (Note 10)	Q _{rr}	_	38.5	_	nC			
DYNAMIC CHARACTERISTICS (Note 10)			•	•	•			
Input Capacitance	C _{iss}	_	635	_	pF	101/11/		
Output Capacitance	Coss		52	_	рF	V _{DS} = -40V, V _{GS} : -f= 1MHz	= UV	
Reverse Transfer Capacitance	Crss		42.5	_	pF]= 11VII 12		
Total Gate Charge (Note 11)	Qg	_	9.6	_	nC	V _{GS} = -5V		
Total Gate Charge (Note 11)	Qg	_	18	_	nC		V _{DS} = -35V	
Gate-Source Charge (Note 11)	Q_{gs}	_	1.77	_	nC	V _{GS} = -10V I _D = -2.1A		
Gate-Drain Charge (Note 11)	Q _{qd}	_	3.66	_	nC			
Turn-On Delay Time (Note 11)	t _{D(on)}	_	2.5	_	ns	V_{DD} = -35V, V_{GS} = -10V I_{D} = -1A, $R_{G} \cong 6.0\Omega$		
Turn-On Rise Time (Note 11)	t _r	_	3.4	_	ns			
Turn-Off Delay Time (Note 11)	t _{D(off)}	_	27.9	_	ns			
Turn-Off Fall Time (Note 11)	t _f	_	8	_	ns			

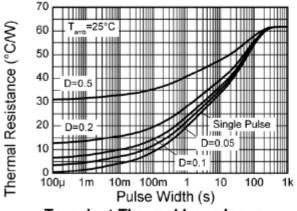
Notes:

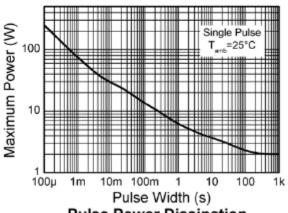
- 6. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 7. Same as note (6), except the device is measured at $t \le 5$ sec.
- 8. Same as note (6), except the device is pulsed with D= 0.05 and pulse width 10µs. The pulse current is limited by the maximum junction temperature.
- 9. Measured under pulsed conditions. Pulse width \leq 300 μ s; duty cycle \leq 2%
- 10. For design aid only, not subject to production testing.
- 11. Switching characteristics are independent of operating junction temperatures.







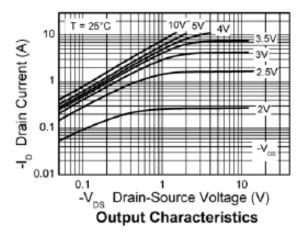


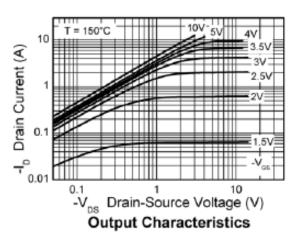


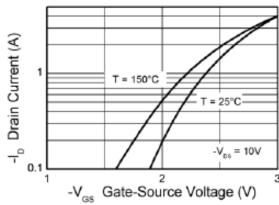
Transient Thermal Impedance

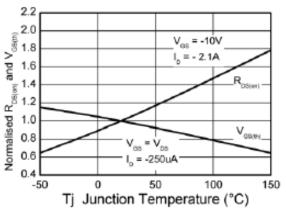
Pulse Power Dissipation





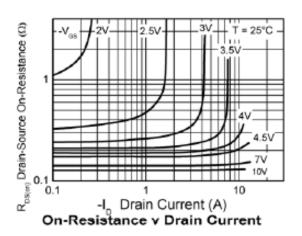


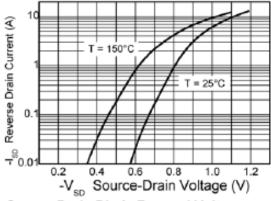




Typical Transfer Characteristics

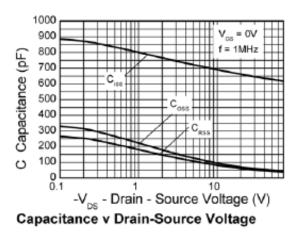
Normalised Curves v Temperature

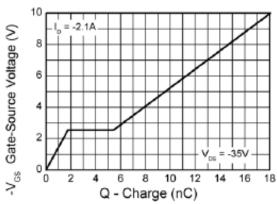




Source-Drain Diode Forward Voltage

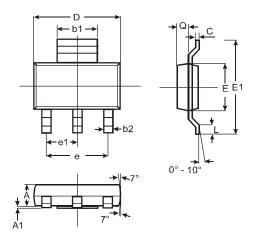






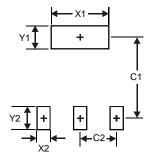
Gate-Source Voltage v Gate Charge

Package Outline Dimensions



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b1	2.90	3.10	3.00		
b2	0.60	0.80	0.70		
C	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	_	_	4.60		
e1		_	2.30		
٦	0.85	1.05	0.95		
Ø	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)		
X1	3.3		
X2	1.2		
Y1	1.6		
Y2	1.6		
C1	6.4		
C2	23		





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